

2SA2046

Silicon PNP epitaxial planer type

For DC-DC converter

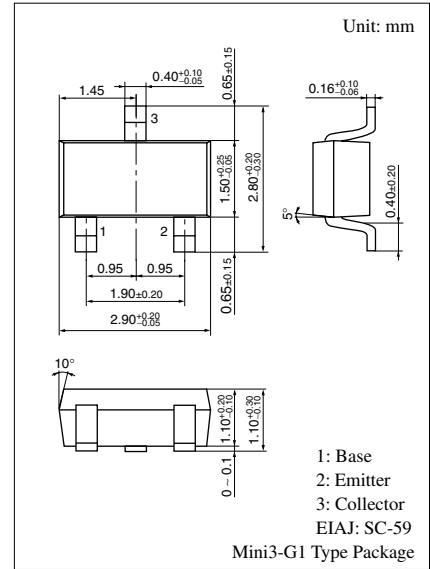
■ Features

- Low collector to emitter saturation voltage $V_{CE(sat)}$
- Mini3-G1 type package, allowing downsizing and thinning of the equipment and automatic insertion through the tape packing

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-30	V
Collector to emitter voltage	V_{CEO}	-20	V
Emitter to base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-5	A
Collector current	I_C	-1.5	A
Collector power dissipation *	P_C	400	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *: Measure on the ceramic substrate at $15 \times 15 \times 0.6 \text{ mm}^3$



Marking Symbol: 3Z

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector to base voltage	V_{CBO}	$I_C = -10 \mu\text{A}$, $I_E = 0$	-30			V
Collector to emitter voltage	V_{CEO}	$I_C = -1 \text{ mA}$, $I_B = 0$	-20			V
Emitter to base voltage	V_{EBO}	$I_E = -10 \mu\text{A}$, $I_C = 0$	-5			V
Forward current transfer ratio *	h_{FE}	$V_{CE} = -2 \text{ V}$, $I_C = -100 \text{ mA}$	160		560	
Collector to emitter saturation voltage *	$V_{CE(sat)}$	$I_C = -500 \text{ mA}$, $I_B = -25 \text{ mA}$		-50	-150	mV
Collector output capacitance	C_{ob}	$V_{CB} = -10 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$		25	35	pF
Transition frequency	f_T	$V_{CB} = -10 \text{ V}$, $I_E = 20 \text{ mA}$, $f = 200 \text{ MHz}$		170		MHz

Note) *: Pulse measurement